

Fariba Hatami

List of Publications by Year in descending order

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79
papers

3,479
citations

236925

25
h-index

133252

59
g-index

79
all docs

79
docs citations

79
times ranked

4790
citing authors

#	ARTICLE	IF	CITATIONS
1	Precise electron beam-based target-wavelength trimming for frequency conversion in integrated photonic resonators. <i>Optics Express</i> , 2022, 30, 6921.	3.4	8
2	Plasma-assisted molecular beam epitaxy of SnO(001) films: Metastability, hole transport properties, Seebeck coefficient, and effective hole mass. <i>Physical Review Materials</i> , 2020, 4, .	2.4	10
3	Inverse-designed photon extractors for optically addressable defect qubits. <i>Optica</i> , 2020, 7, 1805.	9.3	28
4	Deep-level noise characterization of MOVPE-grown $\text{In}^2\text{-Ga}_2\text{O}_3$. <i>Applied Physics Letters</i> , 2019, 115, .	3.3	4
5	Electrical conductivity tensor of $\text{In}^2\text{-Ga}_2\text{O}_3$ analyzed by van der Pauw measurements: Inherent anisotropy, off-diagonal element, and the impact of grain boundaries. <i>Physical Review Materials</i> , 2019, 3, .	2.4	12
6	Frequency Control of Single Quantum Emitters in Integrated Photonic Circuits. <i>Nano Letters</i> , 2018, 18, 1175-1179.	9.1	34
7	Transport properties of doped AlP for the development of conductive AlP/GaP distributed Bragg reflectors and their integration into light-emitting diodes. <i>Applied Physics Letters</i> , 2018, 112, .	3.3	6
8	400%/W second harmonic conversion efficiency in 14 μm -diameter gallium phosphide-on-oxide resonators. <i>Optics Express</i> , 2018, 26, 33687.	3.4	47
9	High Efficient THz Emission From Unbiased and Biased Semiconductor Nanowires Fabricated Using Electron Beam Lithography. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2017, 23, 1-7.	2.9	5
10	Thermal behavior and carrier injection of GaAs/GaP quantum dots light emitting diodes. <i>Applied Physics Letters</i> , 2017, 110, .	3.3	3
11	Nanocavity Integrated van der Waals Heterostructure Light-Emitting Tunneling Diode. <i>Nano Letters</i> , 2017, 17, 200-205.	9.1	129
12	Large-scale GaP-on-diamond integrated photonics platform for NV center-based quantum information. <i>Journal of the Optical Society of America B: Optical Physics</i> , 2016, 33, B35.	2.1	29
13	Biased THz emission from InGaAs nanowires fabricated using electron beam lithography. , 2016, , .		0
14	Efficient Extraction of Zero-Phonon-Line Photons from Single Nitrogen-Vacancy Centers in an Integrated GaP-on-Diamond Platform. <i>Physical Review Applied</i> , 2016, 6, .	3.8	64
15	Selective Epitaxy of InP on Si and Rectification in Graphene/InP/Si Hybrid Structure. <i>ACS Applied Materials & Interfaces</i> , 2016, 8, 26948-26955.	8.0	23
16	Room temperature green to red electroluminescence from (Al,Ga)As/GaP QDs and QWs. <i>Proceedings of SPIE</i> , 2016, , .	0.8	1
17	THz emission from InP and InGaAs nanowires fabricated using electron beam lithography. , 2015, , .		1
18	Thermal annealing effect on the structural properties of epitaxial growth of GaP on Si substrate. <i>Journal of Crystal Growth</i> , 2015, 419, 42-46.	1.5	3

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19	Monolayer semiconductor nanocavity lasers with ultralow thresholds. <i>Nature</i> , 2015, 520, 69-72.	27.8	713
20	Photonic crystal cavity-assisted upconversion infrared photodetector. <i>Optics Express</i> , 2015, 23, 12998.	3.4	10
21	Chemical sensitivity of InP/In _{0.48} Ga _{0.52} P surface quantum dots studied by time-resolved photoluminescence spectroscopy. <i>Journal of Luminescence</i> , 2015, 168, 54-58.	3.1	8
22	Lattice-engineered Si _{1-x} Gex-buffer on Si(001) for GaP integration. <i>Journal of Applied Physics</i> , 2014, 115, 103501.	2.5	10
23	Control of two-dimensional excitonic light emission via photonic crystal. <i>2D Materials</i> , 2014, 1, 011001.	4.4	144
24	Chemical Sensitivity of Luminescent Epitaxial Surface InP Quantum Dots. <i>Journal of Sensor Technology</i> , 2013, 03, 1-5.	1.0	8
25	Photoluminescence sensitivity to methanol vapours of surface InP quantum dot: Effect of dot size and coverage. <i>Sensors and Actuators B: Chemical</i> , 2013, 189, 113-117.	7.8	31
26	AlP/GaP distributed Bragg reflectors. <i>Applied Physics Letters</i> , 2013, 103, 031101.	3.3	8
27	Surface InP/In _{0.48} Ga _{0.52} P quantum dots: Carrier recombination dynamics and their interaction with fluorescent dyes. <i>Journal of Applied Physics</i> , 2013, 114, 163510.	2.5	5
28	Controlling the spontaneous emission rate of monolayer MoS ₂ in a photonic crystal nanocavity. <i>Applied Physics Letters</i> , 2013, 103, 181119.	3.3	194
29	Quasiresonant excitation of InP/InGaP quantum dots using second harmonic generated in a photonic crystal cavity. <i>Applied Physics Letters</i> , 2012, 101, .	3.3	3
30	Single-photon emitters based on epitaxial isolated InP/InGaP quantum dots. <i>Applied Physics Letters</i> , 2012, 100, .	3.3	18
31	A high-resolution spectrometer based on a compact planar two dimensional photonic crystal cavity array. <i>Applied Physics Letters</i> , 2012, 100, 231104.	3.3	73
32	Surface InP Quantum Dots: Effect of Morphology on the Photoluminescence Sensitivity. <i>Procedia Engineering</i> , 2012, 47, 1251-1254.	1.2	5
33	Strong Enhancement of Light-Matter Interaction in Graphene Coupled to a Photonic Crystal Nanocavity. <i>Nano Letters</i> , 2012, 12, 5626-5631.	9.1	248
34	Optical properties of well-isolated single InP/InGaP quantum dots. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012, 9, 1288-1291.	0.8	0
35	Vapour sensing properties of InP quantum dot luminescence. <i>Sensors and Actuators B: Chemical</i> , 2012, 162, 149-152.	7.8	29
36	A hybrid quantum photonic interface for solid state qubits. <i>Proceedings of SPIE</i> , 2011, , .	0.8	0

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37	Distribution of Mn in ferromagnetic (In,Mn)Sb films grown on (001) GaAs using MBE. Journal of Crystal Growth, 2011, 323, 340-343.	1.5	0
38	A comparison of the low frequency noise in InSb grown on GaAs and Si by MBE. Journal of Crystal Growth, 2011, 323, 393-396.	1.5	0
39	Controlled growth of InP/In _{0.48} Ga _{0.52} P quantum dots on GaAs substrate. Journal of Crystal Growth, 2011, 323, 228-232.	1.5	12
40	Second harmonic generation in GaP photonic crystal waveguides. , 2011, , .		2
41	Second harmonic generation in GaP photonic crystal waveguides. Applied Physics Letters, 2011, 98, 263113.	3.3	44
42	Deterministic Coupling of a Single Nitrogen Vacancy Center to a Photonic Crystal Cavity. Nano Letters, 2010, 10, 3922-3926.	9.1	309
43	Sum-frequency generation in doubly resonant GaP photonic crystal nanocavities. Applied Physics Letters, 2010, 97, 043103.	3.3	28
44	Highly polarized self-assembled chains of single layer InP/(In,Ga)P quantum dots. Applied Physics Letters, 2010, 97, 253113.	3.3	11
45	Low frequency noise in InSb/GaAs and InSb/Si channels. Applied Physics Letters, 2010, 97, .	3.3	7
46	Tunable-wavelength second harmonic generation from GaP photonic crystal cavities coupled to fiber tapers. Optics Express, 2010, 18, 12176.	3.4	27
47	Tunable light sources in the visible and near infrared based on fiber taper coupled photonic crystal nanocavities. , 2010, , .		0
48	Second Harmonic Generation in Gallium Phosphide Photonic Crystal Nanocavities with Ultralow CW Pump Power. , 2010, , .		0
49	Evidence of type-I direct recombination in InP/GaP quantum dots via magnetoluminescence. Applied Physics Letters, 2009, 95, 151105.	3.3	12
50	Photoluminescence of InP/GaP quantum dots under extreme conditions. High Pressure Research, 2009, 29, 488-494.	1.2	1
51	Self-assembled chains of single layer InP/(In,Ga)P quantum dots on GaAs (001). Journal of Applied Physics, 2009, 105, 124308.	2.5	15
52	Narrow-gap ferromagnetic semiconductors (In,Mn)Sb on GaAs (001): growth and properties. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 1492-1496.	0.8	3
53	Second harmonic generation in gallium phosphide photonic crystal nanocavities with ultralow continuous wave pump power. Optics Express, 2009, 17, 22609.	3.4	147
54	Lithographic positioning of fluorescent molecules on high-Q photonic crystal cavities. Applied Physics Letters, 2009, 95, 123113.	3.3	26

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55	Probing High-Q Photonic Crystal Resonances with Fluorescent Molecules. , 2009, , .		0
56	Optical Properties of Dilute Nitride InN(As)Sb Quantum Wells and Quantum Dots Grown by Molecular Beam Epitaxy. Journal of Electronic Materials, 2008, 37, 1774-1779.	2.2	6
57	Comparison of MBE Growth of InSb on Si (001) and GaAs (001). Journal of Electronic Materials, 2008, 37, 1799-1805.	2.2	11
58	Single-dot optical emission from ultralow density well-isolated InP quantum dots. Applied Physics Letters, 2008, 93, 143111.	3.3	30
59	Growth and Characterization of InSb films on Si (001). Materials Research Society Symposia Proceedings, 2008, 1068, 1.	0.1	1
60	Colour-tunable light-emitting diodes based on InP/GaP nanostructures. Nanotechnology, 2006, 17, 3703-3706.	2.6	22
61	Mid-infrared luminescence of an InNAsSb ^δ InAs single quantum well grown by molecular beam epitaxy. Applied Physics Letters, 2006, 89, 121912.	3.3	9
62	Biomedical terahertz imaging with a quantum cascade laser. Applied Physics Letters, 2006, 88, 153903.	3.3	133
63	Green emission from InP-GaP quantum-dot light-emitting diodes. IEEE Photonics Technology Letters, 2006, 18, 895-897.	2.5	14
64	Bio-medical imaging with a terahertz quantum cascade laser. , 2006, , .		1
65	Investigation of Optical Properties of Nitrogen Incorporated Sb based Quantum Well and Quantum Dots for Infrared Sensors Application. Materials Research Society Symposia Proceedings, 2006, 955, 1.	0.1	0
66	Investigation of Nitrogen Induced closely coupled Sb based Quantum Dots for Infrared Sensors Application. Materials Research Society Symposia Proceedings, 2006, 959, 1.	0.1	0
67	Comparative Analysis of Bio-Medical Imaging at 3.7 Terahertz with a High Power Quantum Cascade Laser. , 2006, , .		0
68	InSb and InSb:N multiple quantum dots. Applied Physics Letters, 2006, 89, 133115.	3.3	34
69	Light-emitting diodes based on InP quantum dots in GaP(100). , 2005, , .		0
70	Recombination dynamics in self-assembled InP/GaP quantum dots under high pressure. Physica Status Solidi (B): Basic Research, 2004, 241, 3263-3268.	1.5	1
71	Optical properties and carrier dynamics of InP quantum dots embedded in GaP. , 2004, , .		1
72	Shape induced anisotropic elastic relaxation in InP/In _{0.48} Ga _{0.52} P quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 1139-1142.	2.7	1

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73	InP quantum dots in GaP: Growth and luminescence. Materials Science in Semiconductor Processing, 2001, 4, 497-501.	4.0	22
74	Radiative recombination from InP quantum dots on (100) GaP. Applied Physics Letters, 2001, 78, 2163-2165.	3.3	35
75	Optical emission from ultrathin strained type-II InP/GaP quantum wells. Applied Physics Letters, 2001, 79, 2886-2888.	3.3	13
76	Planar ordering of InP quantum dots on (1 0 0)In _{0.48} Ga _{0.52} P. Journal of Crystal Growth, 2000, 216, 26-32.	1.5	39
77	Carrier dynamics in type-II GaSb/GaAs quantum dots. Physical Review B, 1998, 57, 4635-4641.	3.2	231
78	Radiative recombination in type-II GaSb/GaAs quantum dots. Applied Physics Letters, 1995, 67, 656-658.	3.3	313
79	Vapour Sensitivity of InP Surface Quantum Dots. Key Engineering Materials, 0, 605, 177-180.	0.4	4